

Low VF Schottky Diode Array

- Reverse voltage: 30 V
- Forward current: 0.9 A
- Small diode quad array for polarity independence, reverse polarity protection and low loss bridge rectification
- Very low forward voltage:
 0.5 V typ. @ 0.7 A (per diode)
- Fast switching
- Pb-free (ROHS compliant) package¹⁾
- Qualified according AEC Q101



BAS3007A-RPP



| TIT | |
|-----|--|

| Туре | Package | Configuration | Marking |
|--------------|---------|---------------|---------|
| BAS3007A-RPP | SOT143 | bridge | E1s |

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

| Parameter | Symbol | Value | Unit | |
|---|---------------------|---------|------|--|
| Diode reverse voltage ²⁾ | V _R | 30 | V | |
| Peak reverse voltage ²⁾ | V _{RM} | 30 | | |
| RMS reverse voltage ²⁾ | V _{R(RMS)} | 21 | | |
| Forward current ²⁾ | I _F | | mA | |
| $T_{\rm S} \le 46^{\circ}{\rm C}$ | | 900 | | |
| $T_{S} \leq 82^{\circ}C$ | | 700 | | |
| Non-repetitive peak surge forward current | / _{FSM} | 5 | А | |
| (<i>t</i> ≤ 10 ms) | | | | |
| Junction temperature | T _i | 150 | °C | |
| Storage temperature | T _{stg} | -65 150 | | |

¹Pb-containing package may be available upon special request

²For $T_A > 25^{\circ}$ C the derating of V_R and I_F has to be considered. Please refer to the attached curves.



Thermal Resistance

| Parameter | Symbol | Value | Unit |
|--|-------------------|-------|------|
| Junction - soldering point ¹⁾ | R _{thJS} | ≤ 95 | K/W |

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

| Symbol | Values | | | Unit |
|----------------|--------|------|-----------|----------------|
| | min. | typ. | max. | |
| | | | | |
| I _R | | | | μA |
| | - | - | 30 | |
| | | min. | min. typ. | min. typ. max. |

| V _R = 30 V | | - | - | 350 | |
|---|----------------|---|------|------|---|
| Forward voltage (per diode) ²⁾³⁾ | V _F | | | | V |
| <i>I</i> _F = 100 mA | | - | 0.35 | 0.4 | |
| / _F = 350 mA | | - | 0.4 | 0.5 | |
| <i>I</i> _F = 500 mA | | - | 0.45 | 0.55 | |
| <i>I</i> _F = 700 mA | | - | 0.5 | 0.6 | |
| <i>I</i> _F = 900 mA | | - | 0.6 | 0.7 | |

AC Characteristics

| Diode capacitance (per diode) | CT | - | 9 | 15 | pF |
|--|----|---|---|----|----|
| V _R = 5 V, <i>f</i> = 1 MHz | | | | | |

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

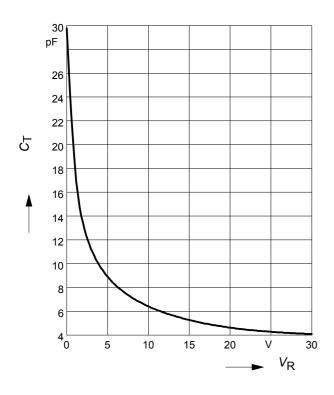
²Pulsed test, t_p = 300 µs; *D* = 0.01

³When used as shown for Reverse Polarity Protection (RPP, see page 4), the voltage available to the circuit being protected will be two diode drops below the power supply voltage. In other words, the supply current will pass through two diodes.



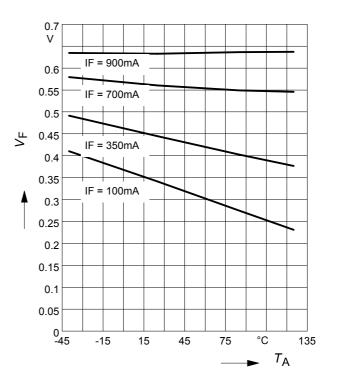
Diode capacitance $C_T = f(V_R)$

f = 1MHz (per diode)

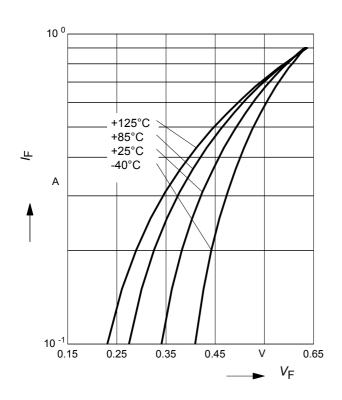


Forward Voltage $V_{\rm F}$ = $f(T_{\rm A})$

 $I_{\rm F}$ = Parameter (per diode)



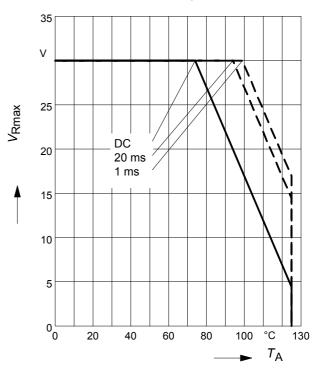
Forward current $I_F = f(V_F)$ T_A = Parameter (per diode)



Permissible Reverse voltage $V_R = f(T_A)$

 t_p = Paramter, Duty cycle < 0.01

Device mounted on PCB with R_{th} = 160 K/W



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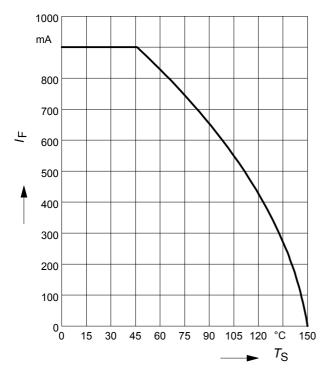




Forward current $I_{\rm F}$ = $f(T_{\rm S})$

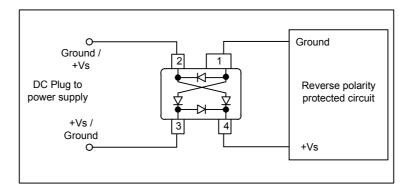
Current flows through two chips

per package at the same time (per array)

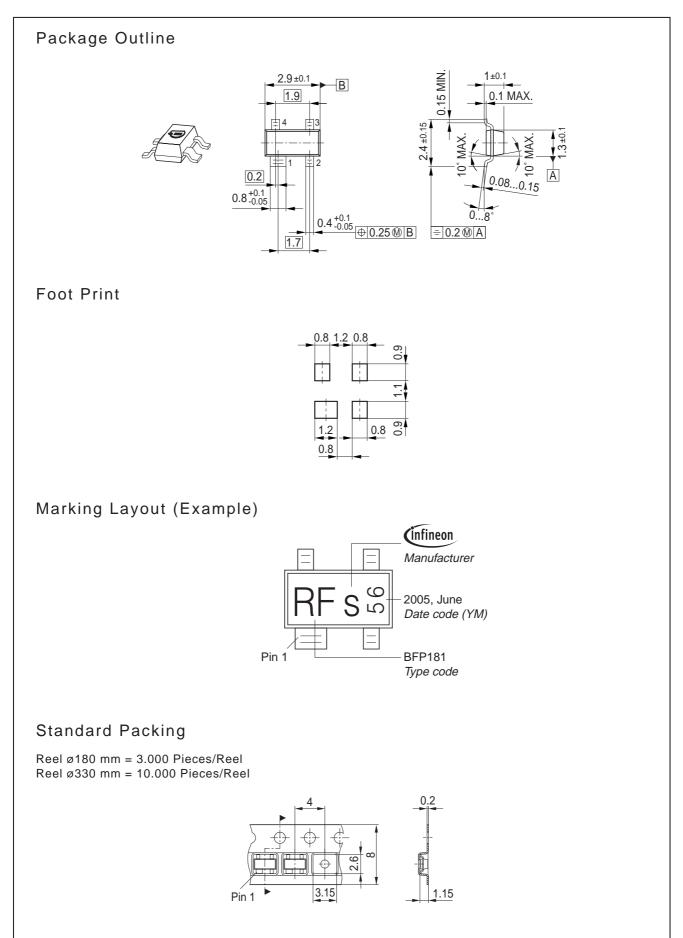


Application example BAS3007A-RPP

Advanced Reverse Polarity Protection(RPP): due to diode orientation, circuit at the right will be protected from damage and will also function normally in the event reverse polarity is applied to pins 2 and 3 of the BAS3007A-RPP.









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